## REMARKS

The specification has been amended to correct errors of a typographical and grammatical nature. Due to the number of corrections thereto, applicants submit herewith a Substitute Specification, along with a marked-up copy of the original specification for the Examiner's convenience. The substitute specification includes the changes as shown in the marked-up copy and includes no new matter. Therefore, entry of the Substitute Specification is respectfully requested.

The abstract has been amended to correct an error of a grammatical nature.

Entry of the preliminary amendments and examination of the application is respectfully requested.

Attached hereto is a marked-up version of the change made to claim 10 by the current amendment. The attached page is captioned "Version with Markings to Show Changes Made".

To the extent necessary, Applicant's petition for an extension of time under 37 CFR 1.136. Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account No. 01-2135 (501.39983X00) and please credit any excess fees to such deposit account.



Respectfully submitted,

ANTONELLI, TERRY, STOUT & KRAUS, LLP

Gregory E. Montone Registration No. 28,141

GEM:alw (703) 312-6600



## ATTACHMENT A

## VERSION WITH MARKINGS TO SHOW CHANGES MADE

## In the Claims

Claim 10 has been amended as indicated below:

10. (Amended) A method of manufacturing a semiconductor device of laminating to form a bottom electrode, a dielectric and a top electrode on substrate having a three-dimensional structive structure in which,

the bottom electrode and the top electrode are formed by using a starting precursor in which a starting metalorganic material containing a \( \mathbb{B}\)-diketone complex is dissolved in tetrahydrofuran, toluene, hexane or octane, by a liquid carrying and evaporation, metalorganic chemical vapor deposition process.